

PN3567

NPN General Purpose Amplifier

- This device is for use as a medium amplifier and switch requiring collector currents up 300mA.
- Sourced from process 19.



1. Emitter 2. Base 3. Collector

Absolute Maximum Ratings T_A =25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	40	V
V _{CBO}	Collector-Base Voltage	80	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current - Continuous	600	mA
T _{J,} T _{STG}	Operating and Storage Junction Temperature Range	- 55 ~ 150	°C

Electrical Characteristics $T_A=25^{\circ}C$ unless otherwise noted

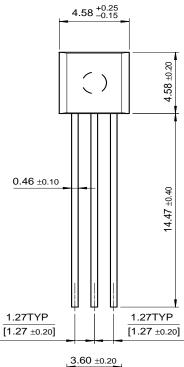
collector-Emitter Breakdown Voltage * Collector-Base Breakdown Voltage Emitter-Base Breakdown Voltage	$I_C = 30 \text{mA}, I_B = 0$ $I_C = 100 \mu \text{A}, I_E = 0$ $I_E = 10 \mu \text{A}, I_C = 0$	40 80			V
Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_E = 0$	80			
Ů					
mitter-Base Breakdown Voltage	I= = 10uA I= = 0	-		l	V
	ιΕ – τομον, ιζ – ο	5			V
Collector Cut-off Current	$V_{CB} = 40V, I_{E} = 0$			50	nA
	<u> </u>				μΑ
mitter Cut-off Current	$V_{EB} = 4V, I_{C} = 0$			25	nA
ristics					
OC Current Gain	$V_{CE} = 1V, I_{C} = 150mA$	40		120	
	$V_{CE} = 1V$, $I_{C} = 30mA$	40			
Collector-Emitter Saturation Voltage *	I _C = 150mA, I _B = 15mA			0.25	V
Base-Emitter On Voltage	V _{CE} = 1V, I _C = 150mA			1.1	V
Characteristics					
Output Capacitance	$V_{CB} = 10V, I_{E} = 0$			20	pF
nput Capacitance	$V_{EB} = 0.5V, I_{C} = 0$			80	
) Si O	mitter Cut-off Current ristics C Current Gain ollector-Emitter Saturation Voltage * ase-Emitter On Voltage Characteristics utput Capacitance	$V_{CB} = 40V, \ I_E = 0, \ T_A = 75^{\circ}C$ mitter Cut-off Current $V_{EB} = 4V, \ I_C = 0$ ristics $C \ \text{Current Gain} \qquad V_{CE} = 1V, \ I_C = 150\text{mA} \\ V_{CE} = 1V, \ I_C = 30\text{mA}$ ollector-Emitter Saturation Voltage * $I_C = 150\text{mA}, \ I_B = 15\text{mA}$ ase-Emitter On Voltage $V_{CE} = 1V, \ I_C = 150\text{mA}$ Characteristics utput Capacitance $V_{CB} = 10V, \ I_E = 0$ uput Capacitance $V_{EB} = 0.5V, \ I_C = 0$	$V_{CB} = 40 \text{V}, \ I_E = 0, \ T_A = 75 ^{\circ}\text{C}$ mitter Cut-off Current $V_{EB} = 4 \text{V}, \ I_C = 0$ ristics $C \text{ Current Gain} \qquad V_{CE} = 1 \text{V}, \ I_C = 150 \text{mA} \qquad 40$ $V_{CE} = 1 \text{V}, \ I_C = 30 \text{mA} \qquad 40$ ollector-Emitter Saturation Voltage * $I_C = 150 \text{mA}, \ I_B = 15 \text{mA}$ ase-Emitter On Voltage $V_{CE} = 1 \text{V}, \ I_C = 150 \text{mA}$ $V_{CE} = 1 \text{V}, \ I_C = 150 \text{mA}$ $V_{CE} = 1 \text{V}, \ I_C = 150 \text{mA}$ $V_{CE} = 1 \text{V}, \ I_C = 150 \text{mA}$ $V_{CE} = 10 \text{V}, \ I_C = 0$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$

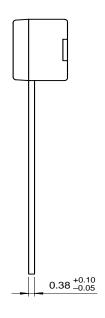
^{*} Pulse Test: Pulse Width \leq 300ms, Duty Cycle \leq 2.0%

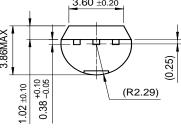
Thermal Characteristics T _A =25°C unless otherwise noted			
Symbol	Parameter	Max.	Units
P _D	Total Device Dissipation Derate above 25°C	625 5	mW mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	83.3	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	200	°C/W

Package Dimensions

TO-92







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